

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK063Z60Z1

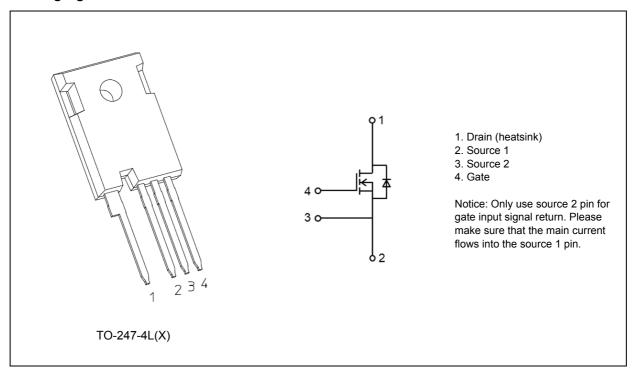
1. Applications

· Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.053 \Omega$ (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_{D} = 1.47 mA)

3. Packaging and Internal Circuit



1

Start of commercial production



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | |
|--------------------------------|-------------------------|------------------|------------|-------|
| Drain-source voltage | | V_{DSS} | 600 | V |
| Gate-source voltage | , | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | I _D | 37 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 148 | |
| Power dissipation (7 | Γ _c = 25 °C) | P _D | 242 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 609 | mJ |
| Single-pulse avalanche current | | I _{AS} | 6.1 | Α |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 37 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 148 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |
| Mounting torque | | TOR | 0.8 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.515 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 50 | |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 29 mH, I_{AS} = 6.1 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|-------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 2 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | _ | V |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 1.47 mA | 3 | _ | 4 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 12.8 A | _ | 0.053 | 0.063 | Ω |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------|--------------------|---|-----|------|-----|------|
| Input capacitance | | C _{iss} | $V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$ | _ | 3200 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | | _ | 3 | _ | |
| Output capacitance | | C _{oss} | | _ | 77 | _ | |
| Effective output capacitance (energy related) | (Note 3) | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 128 | - | |
| Effective output capacitance (time related) | (Note 4) | C _{o(tr)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 910 | | |
| Gate resistance | | r _g | V _{DS} = OPEN , f = 1 MHz | _ | 2.5 | _ | Ω |
| Switching time (rise time) | | t _r | See Fig. 6.2.1 | _ | 22 | _ | ns |
| Switching time (turn-on time) | | t _{on} | | _ | 55 | _ | |
| Switching time (fall time) | | t _f | | _ | 5 | _ | |
| Switching time (turn-off time) | | t _{off} | | _ | 105 | _ | |
| MOSFET dv/dt ruggedness | | dv/dt | $V_{DS} \le V_{DSS}, I_D \le 18.5 A$ | 120 | _ | | V/ns |

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.

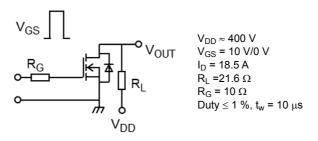


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_{g} | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 37 \text{ A}$ | ı | 56 | I | nC |
| Gate-source charge 1 | Q _{gs1} | | | 18 | | |
| Gate-drain charge | Q_{gd} | | _ | 15 | _ | |

Rev.1.0



6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|-----------------|---|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 37 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | | V _{DD} = 400 V, | _ | 350 | _ | ns |
| Reverse recovery charge | Q_{rr} | I_{DR} = 18.5 A, V_{GS} = 0 V -d I_{DR} /dt = 100 A/ μ s | _ | 5.3 | _ | μС |
| Peak reverse recovery current | I _{rr} | -αιρκ/αι – 100 Α/μ3 | | 30 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | $V_{DD} \le 400 \text{ V}, I_{DR} \le 18.5 \text{ A}, V_{GS} = 0 \text{ V}$ | 40 | | _ | V/ns |

7. Marking (Note)

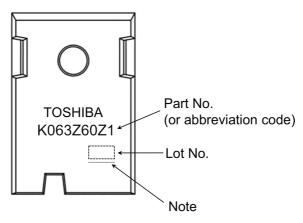


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

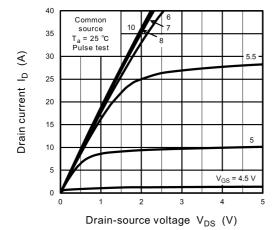


Fig. 8.1 I_D - V_{DS}

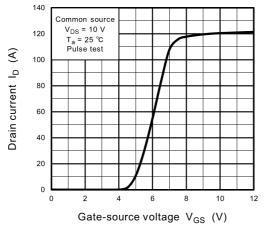


Fig. 8.3 I_D - V_{GS}

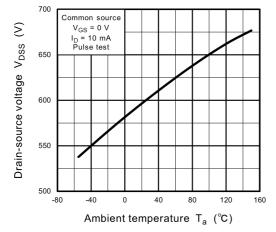


Fig. 8.5 V_{DSS} - T_a

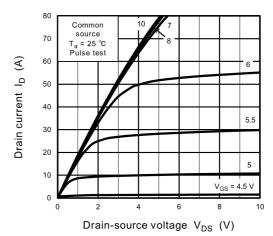


Fig. 8.2 I_D - V_{DS}

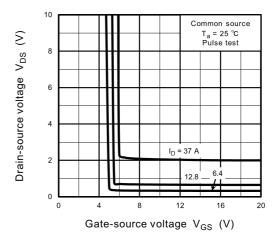


Fig. 8.4 V_{DS} - V_{GS}

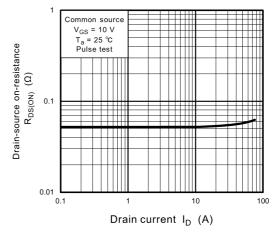
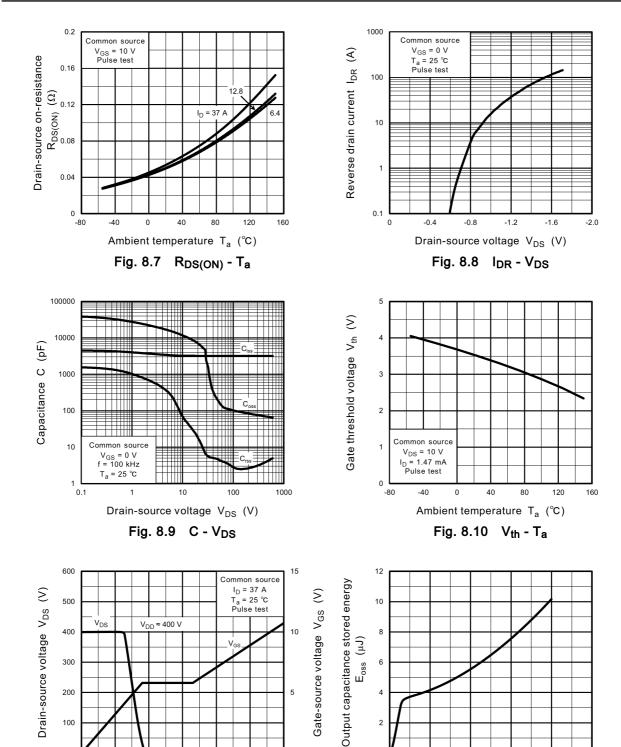


Fig. 8.6 R_{DS(ON)} - I_D





Total gate charge Q_q (nC) **Dynamic Input/Output Characteristics**

30

20

Drain-source voltage V_{DS} (V) Fig. 8.12 Eoss - V_{DS}

200

100

0

0

60

0



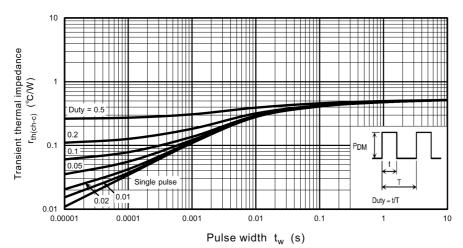


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

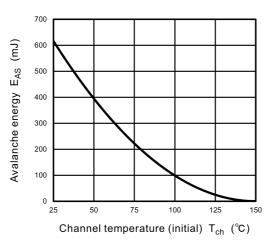


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

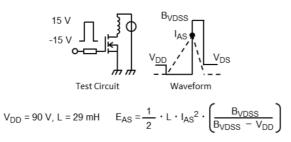


Fig. 8.16 Test Circuit/Waveform

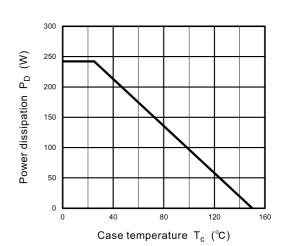


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

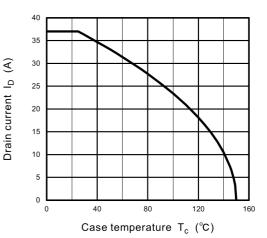


Fig. 8.17 I_D - T_c (Guaranteed Maximum)



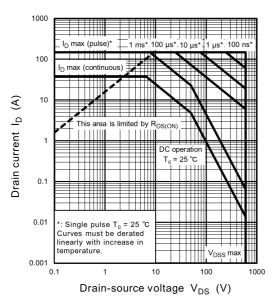


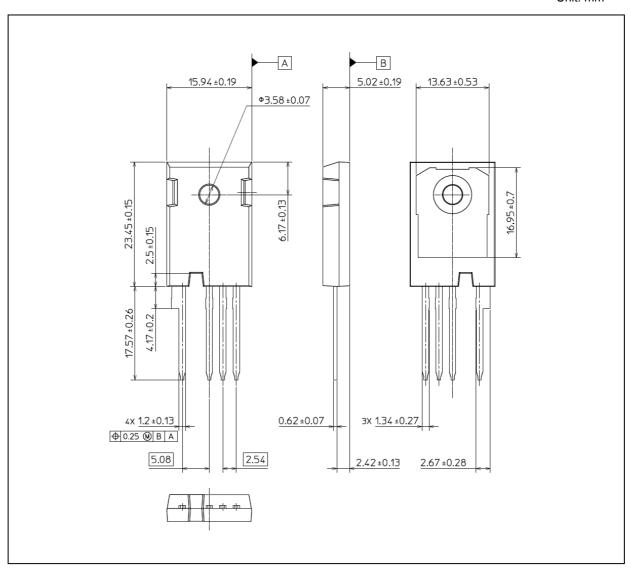
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.55 g (typ.)

| Package Name(s) |
|------------------------|
| TOSHIBA: 2-16M3A |
| Nickname: TO-247-4L(X) |



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